Vishay Semiconductors

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Cathode O Anode

## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	1 A			
V <sub>R</sub>	600 V			
V <sub>F</sub> at I <sub>F</sub>	0.83 V			
t <sub>rr</sub>	55 ns			
T <sub>J</sub> max.	175 °C			
Package	SMF (DO-219AB)			
Circuit configuration	Single			

## FEATURES

Ultrafast recovery time, reduced Q<sub>rr</sub>, and soft recovery



FREE

- 175 °C maximum operating junction temperature
- For PFC CRM, snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Wave and reflow solderable
- Compatible to SOD-123W package case outline
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

State of the art ultrafast recovery rectifiers designed with optimized performance of forward voltage drop, ultrafast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC, boost, lighting, in the AC/DC section of SMPS, freewheeling and clamp diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

## **MECHANICAL DATA**

Case: SMF (DO-219AB)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V <sub>RRM</sub>		600	V	
Average rectified forward current	I <sub>F(AV)</sub>	$T_{\rm C} = 158 \ ^{\circ}{\rm C} \ ^{(1)}$	1	٨	
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 6 ms square pulse	30	A	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	

Note

<sup>(1)</sup> Device on PCB with 8 mm x 16 mm soldering lands

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$	I <sub>R</sub> = 100 μA	600	-	-	
Forward voltage	V	I <sub>F</sub> = 1 A	-	1.0	1.2	V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 1 A, T <sub>J</sub> = 150 °C	-	0.83	1	
Reverse leakage current I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	-	3		
	'R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	20	100	μA
Junction capacitance	CT	V <sub>R</sub> = 600 V	-	5	-	pF

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	42	-	
Reverse recovery time		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	55	20
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	32	-	ns
		T <sub>J</sub> = 125 °C		-	47	-	
Peak recovery current I <sub>RRM</sub>	1	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 1 A dI <sub>F</sub> /dt = 500 A/μs V <sub>R</sub> = 400 V	-	4.8	-	А
	IRRM	T <sub>J</sub> = 125 °C		-	6.8	-	~
	Reverse recovery charge Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	77	-	nC
neverse recovery charge		T <sub>J</sub> = 125 °C		-	160	-	nc

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistance, junction to mount	$R_{thJM}$	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	15	°C/W
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	130	°C/W
Approximate weight				0.015	-	g
				0.0005		oz.
Marking device		Case style SMF (DO-219AB)	MNU			

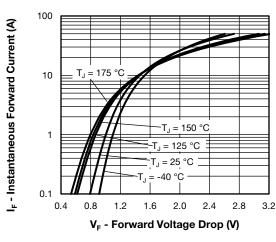


Fig. 1 - Typical Forward Voltage Drop Characteristics

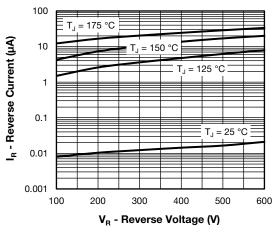


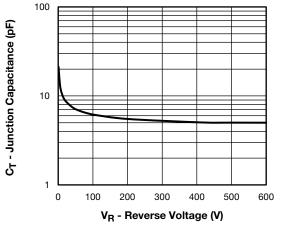
Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

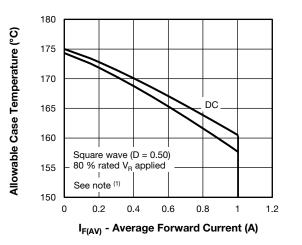


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

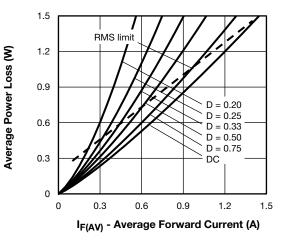


Fig. 5 - Forward Power Loss Characteristics

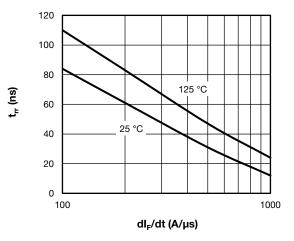


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

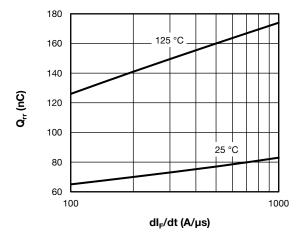


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

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<sup>&</sup>lt;sup>(2)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $<sup>\</sup>begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \ \mathsf{-D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

# VS-1EFU06-M3

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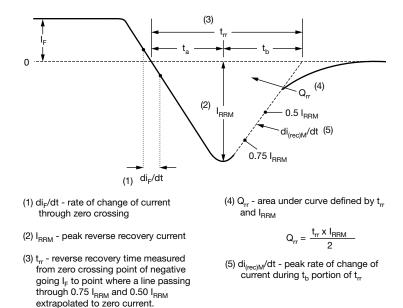
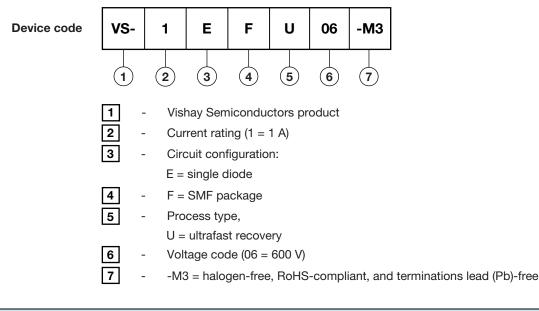


Fig. 8 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

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ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-1EFU06-M3/I	10 000	10 000	13" diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95572			
Part marking information	www.vishay.com/doc?95618			
Packaging information	www.vishay.com/doc?95577			
SPICE model	www.vishay.com/doc?96867			

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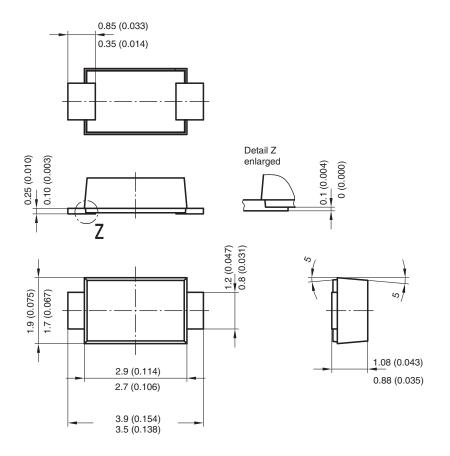
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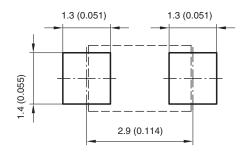
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# SMF (DO-219AB)

#### **DIMENSIONS** in millimeters (inches)



Foot print recommendation:



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